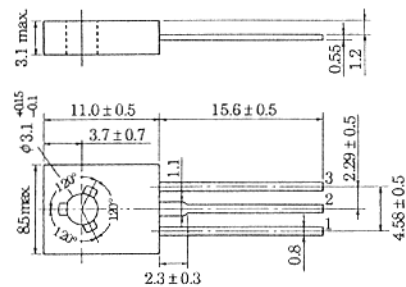


2SC1212, 2SC1212A

SILICON NPN EPITAXIAL
LOW FREQUENCY POWER AMPLIFIER



- 1. Emitter
 - 2. Collector
 - 3. Base
- (Dimensions in mm)

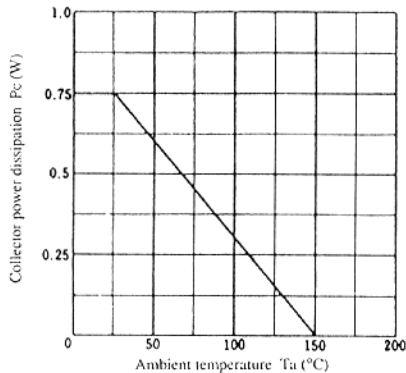
(JEDEC TO-126 MOD.)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC1212	2SC1212A	Unit
Collector to base voltage	V _{CBO}	50	80	V
Collector to emitter voltage	V _{CEO}	50	80	V
Emitter to base voltage	V _{EBO}	4	4	V
Collector current	I _C	1	1	A
Collector power dissipation	P _C	0.75	0.75	W
	P _C *	8	8	W
Junction temperature	T _j	150	150	°C
Storage temperature	T _{stg}	-55 to +150	-55 to +150	°C

* Value at T_C = 25°C

MAXIMUM COLLECTOR DISSIPATION
CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

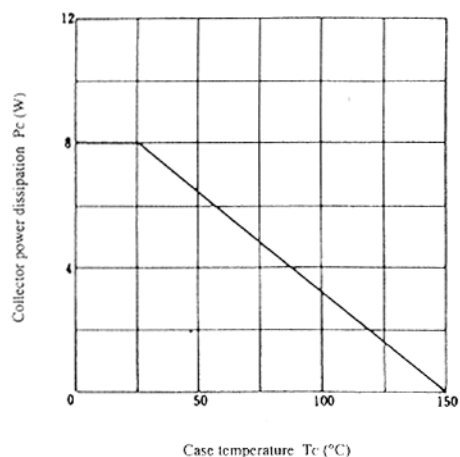
Item	Symbol	Test Condition	2SC1212			2SC1212A			Unit
			min.	typ.	max.	min.	typ.	max.	
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = 1mA, I _E = 0	50	—	—	80	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = 10mA, R _{BE} = ∞	50	—	—	80	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = 1mA, I _C = 0	4	—	—	4	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = 50V, I _E = 0	—	—	5	—	—	5	μA
DC current transfer ratio	h _{FE} *	V _{CE} = 4V, I _C = 50mA	60	—	200	60	—	200	
	h _{FE}	V _{CE} = 4V, I _C = 1A (pulse test)	20	—	—	20	—	—	
Base to emitter voltage	V _{BE}	V _{CE} = 4V, I _C = 50mA	—	0.65	1.0	—	0.65	1.0	V
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 1A, I _B = 0.1A (pulse test)	—	0.75	1.5	—	0.75	1.5	V
Gain bandwidth product	f _T	V _{CE} = 4V, I _C = 30mA	—	160	—	—	160	—	MHz

* The 2SC1212 and 2SC1212A are grouped by h_{FE} as follows.

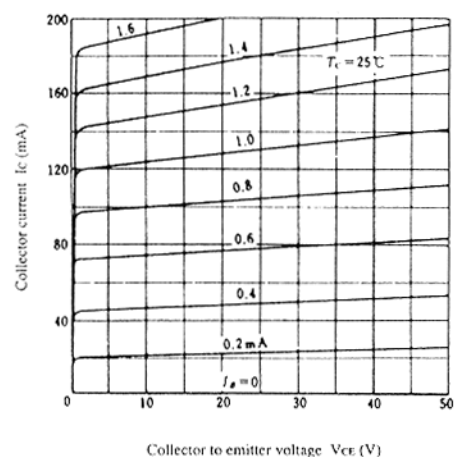
B	C
60 to 120	100 to 200

2SC1212, 2SC1212A

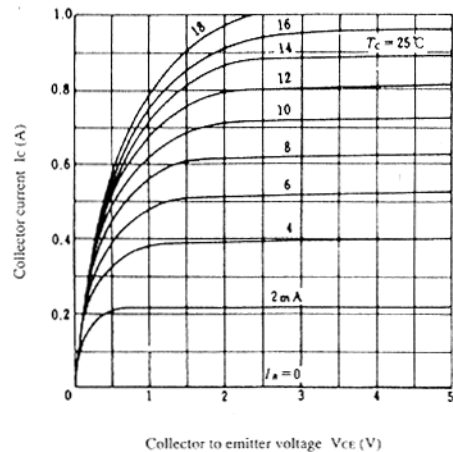
MAXIMUM COLLECTOR DISSIPATION CURVE



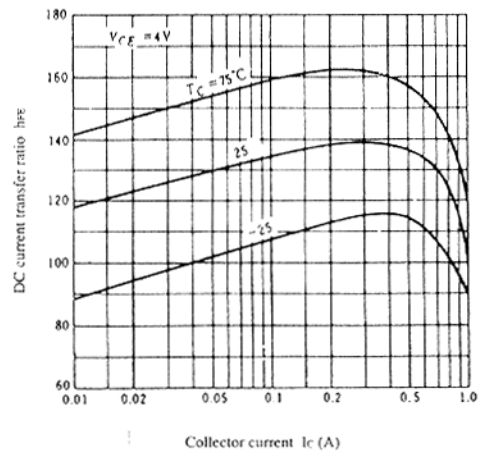
TYPICAL OUTPUT CHARACTERISTICS



TYPICAL OUTPUT CHARACTERISTICS



DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



TYPICAL TRANSFER CHARACTERISTICS

